

Title (en)
METHOD FOR PRODUCING SILICON WAFER

Title (de)
HERSTELLUNGSVERFAHREN FÜR EINEN SILIZIUMWAFER

Title (fr)
PROCÉDÉ DE FABRICATION D'UNE PLAQUE DE SILICIUM

Publication
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Application
EP 05745693 A 20050603

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• JP 2005010215 W 20050603
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Abstract (en)
[origin: EP1758154A1] The present invention is a method for producing a silicon wafer from a silicon single crystal, at least comprising, a double-side polishing step of mirror-polishing both sides of a wafer sliced from the silicon single crystal, a heat treatment step of heat-treating the mirror-polished wafer, and a repolishing step of polishing again a front surface or the both sides of the heat-treated wafer. There is provided a method for producing a silicon wafer by which a silicon wafer of high quality in which COP-free region or oxide precipitate-free region is sufficiently ensured and in which also neither haze nor foreign body sticking is on a wafer front surface and further in which no contact trace with a jig is on a wafer back surface can be produced.

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